Lung-Hsing Hsu

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/1689562/publications.pdf

Version: 2024-02-01

1163117 1281871 26 211 8 11 citations h-index g-index papers 26 26 26 184 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Review of Silicon Carbide Processing for Power MOSFET. Crystals, 2022, 12, 245.	2.2	50
2	Development of GaN HEMTs Fabricated on Silicon, Silicon-on-Insulator, and Engineered Substrates and the Heterogeneous Integration. Micromachines, 2021, 12, 1159.	2.9	34
3	Influence of the microstructure geometry of patterned sapphire substrates on the light extraction efficiency of GaN LEDs. Applied Optics, 2016, 55, 7387.	2.1	25
4	The Evolution of Manufacturing Technology for GaN Electronic Devices. Micromachines, 2021, 12, 737.	2.9	23
5	InN-based heterojunction photodetector with extended infrared response. Optics Express, 2015, 23, 31150.	3.4	21
6	Enhanced photocurrent of a nitride–based photodetector with InN dot-like structures. Optical Materials Express, 2014, 4, 2565.	3.0	18
7	Enhanced power conversion efficiency in InGaN-based solar cells via graded composition multiple quantum wells. Optics Express, 2015, 23, A1434.	3.4	15
8	Site-controlled crystalline InN growth from the V-pits of a GaN substrate. Applied Surface Science, 2017, 405, 449-454.	6.1	10
9	Light Extraction Enhancement of GaN-Based Light-Emitting Diodes Using Crown-Shaped Patterned Sapphire Substrates. IEEE Photonics Technology Letters, 2012, 24, 1212-1214.	2.5	8
10	Effect of Sputtered AlN Location on the Growth Mechanism of GaN. ECS Journal of Solid State Science and Technology, 2017, 6, R131-R134.	1.8	6
11	Enhanced light harvesting of nitride-based nanopillars covered with ZnO using indium–tin oxide nanowhiskers. Japanese Journal of Applied Physics, 2014, 53, 04ER10.	1.5	1
12	Numerical study of GaAs-based dual junction intermediate band solar cells. , 2012, , .		0
13	Embedded InN dot-like structure within InGaN layers using gradient-Indium content in nitride-based solar cell. , 2013, , .		O
14	Embedded InN dot-like structures with modulating growth temperature in nitride-based solar cell. , $2014, , .$		0
15	Purely sidewall InGaN/GaN core-shell nanorod green light-emitting diodes. , 2015, , .		O
16	Optical influence of a hybrid ZnO / indium-tin-oxide nano-rod and whisker. , 2015, , .		0
17	Optical properties of InN-based photodetection devices. , 2015, , .		O
18	InN nanopillar devices with strong photoresponse. , 2016, , .		0

#	Article	IF	CITATIONS
19	Numerical study on doping and positioning effect of type-II GaSb/GaAs quantum ring layer on solar cell performances. , 2016 , , .		O
20	Enhanced Photoresponse of InN Devices Using Indium-Tin Oxide Nanorods. , 2017, , .		0
21	Optical Properties of Patterned InN in Photodetection Devices. , 2018, , .		O
22	A ZnO/InN/GaN Heterojunction Photodetector with Extended Infrared Response., 2015,,.		0
23	Site-controlled crystalline growth of InN on GaN substrate and its photoluminscence. , 2016, , .		O
24	A Single InN Nanopillar Photodetector with Extended Infrared Response Grown by MOCVD., 2016,,.		0
25	InN Nanopillar Photodetector with Enhanced Infrared Response Using Indium-Tin Oxide Nanorods. , 2017, , .		O
26	III–V Nitride-Based Photodetection. Series in Optics and Optoelectronics, 2017, , 597-613.	0.0	0